



UTT150N03

Preliminary

Power MOSFET

N-CHANNEL ENHANCEMENT MODE POWER MOSFET

DESCRIPTION

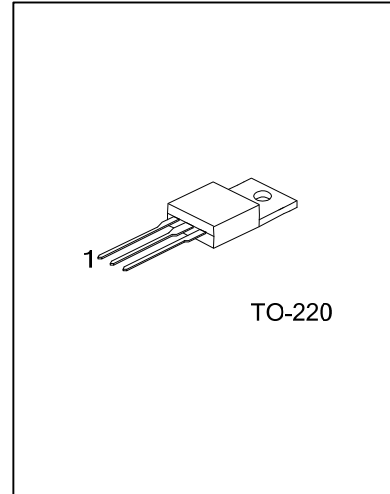
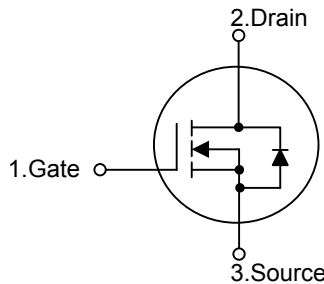
The UTC **UTT150N03** is a N-channel power MOSFET, using UTC's advanced trench technology to provide customers with a minimum on-state resistance, low gate charge and superior switching performance.

The UTC **UTT150N03** is generally applied in DC to DC convertor, synchronous or conventional switching PWM controllers.

FEATURES

- * 150A, 30V, $R_{DS(ON)}=4.1m\Omega @ V_{GS}=10V, I_D = 75A$
 $R_{DS(ON)}=4.6m\Omega @ V_{GS}=4.5V, I_D = 75A$
- * High Switching Speed
- * High Power and Current Handling Capability
- * RoHS Compliant

SYMBOL



ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UTT150N03L-TA3-T	UTT150N03G-TA3-T	TO-220	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

UTT150N03L-TA3-T	(1)Packing Type	(1) T: Tube
	(2)Package Type	(2) TA3: TO-220
	(3)Lead Free	(3) G: Halogen Free, L: Lead Free

■ ABSOLUTE MAXIMUM RATINGS ($T_C=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	30	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current	Continuous	I_D	150	A
	Pulsed	I_{DM}	266	A
Single Pulsed Avalanche Energy (Note 2)		E_{AS}	300	mJ
Power Dissipation	Power Dissipation	P_D	160	W
	Derate above 25°C		1.07	W/ $^{\circ}\text{C}$
Junction Temperature		T_J	+150	$^{\circ}\text{C}$
Storage Temperature		T_{STG}	-55~+150	$^{\circ}\text{C}$

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	62	$^{\circ}\text{C}/\text{W}$
Junction to Case	θ_{JC}	0.94	$^{\circ}\text{C}/\text{W}$

■ ELECTRICAL CHARACTERISTICS (T_c=25°C, unless otherwise noted)

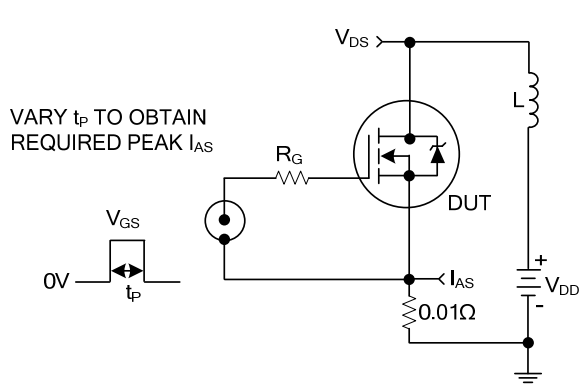
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	I _D =250μA, V _{GS} =0V	30			V	
Drain-Source Leakage Current	I _{DSS}	V _{DS} =24V, V _{GS} =0V			1	μA	
Gate- Source Leakage Current	Forward	I _{GSS}			+100	nA	
	Reverse				-100	nA	
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	1		3	V	
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =75A		3.4	4.1	mΩ	
		V _{GS} =4.5V, I _D =75A		4.0	4.6		
DYNAMIC PARAMETERS							
Input Capacitance	C _{ISS}	V _{GS} =0V, V _{DS} =15V, f=1.0MHz		5200		pF	
Output Capacitance	C _{OSS}			970		pF	
Reverse Transfer Capacitance	C _{RSS}			570		pF	
SWITCHING PARAMETERS							
Gate Resistance	R _G	V _{GS} =0.5V, f=1MHz		2.1		Ω	
Total Gate Charge	Q _{G(TOT)}	V _{GS} =0~10V, V _{DD} =15V, I _D =75A, I _G =1mA		106	132	nC	
	Q _{G(5)}	V _{GS} =0~5V, V _{DD} =15V, I _D =75A, I _G =1mA		56	69	nC	
Threshold Gate Charge	Q _{G(TH)}	V _{GS} =0~1V, V _{DD} =15V, I _D =75A, I _G =1mA		5.0	6.5	nC	
Gate to Source Charge	Q _{GS}	V _{DD} =15V, I _D =75A, I _G =1mA		15		nC	
Gate Charge Threshold to Plateau	Q _{GS2}			10		nC	
Gate to Drain Charge	Q _{GD}			23		nC	
Turn-ON Time	t _{ON}					168	ns
Turn-ON Delay Time	t _{D(ON)}	V _{DD} =15V, I _D =75A, V _{GS} =4.5V, R _{GS} =3.3Ω		11		ns	
Rise Time	t _R			105		ns	
Turn-OFF Delay Time	t _{D(OFF)}			70		ns	
Fall-Time	t _F			46		ns	
Turn-OFF Time	t _{OFF}					173	ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Drain-Source Diode Forward Voltage	V _{SD}	I _S =150A			1.25	V	
		I _S =15A			1.0	V	
Body Diode Reverse Recovery Time	t _{RR}	I _{SD} =150A, dI _{SD} /dt=100A/μs			37	ns	
Body Diode Reverse Recovery Charge	Q _{RR}				21	nC	

Notes: 1. Package current limitation is 80A.

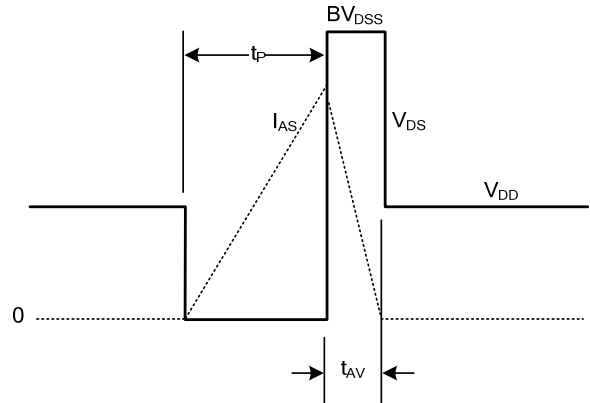
2. Starting T_J = 25°C, L = 0.15mH, I_{AS} = 64A, V_{DD} = 27V, V_{GS}=10V

3. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%

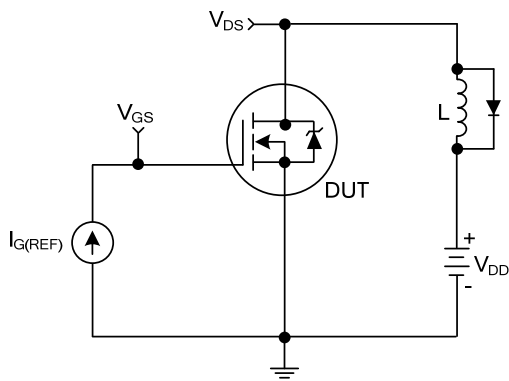
TEST CIRCUITS AND WAVEFORMS



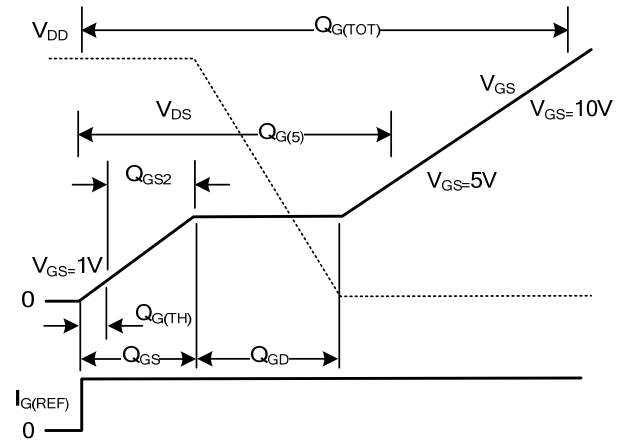
Unclamped Energy Test Circuit



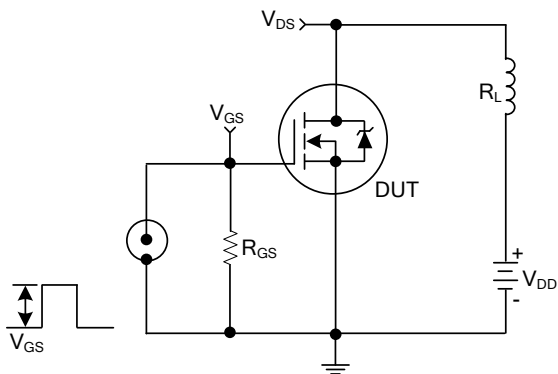
Unclamped Energy Waveforms



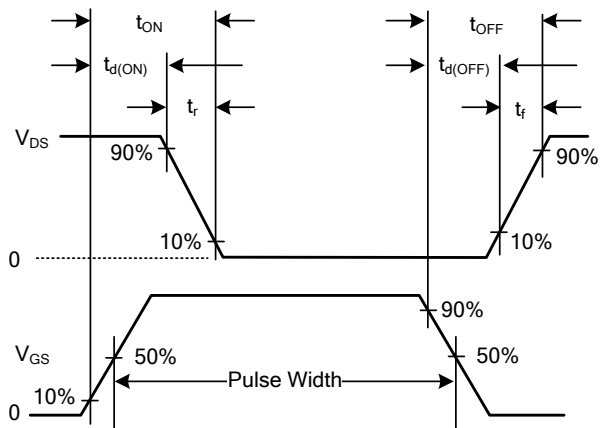
Gate Charge Test Circuit



Gate Charge Waveforms



Switching Time Test Circuit



Switching Time Waveforms

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